



JA11001700P52; 1.1-1.7 GHz 150W AMPLIFIER

- Solid-state Class AB design
- GaN on SiC Transistors
- High reliability and ruggedness
- Forward/Reflected Power Monitorings
- Temperature and Current Monitorings
- Fast Switching Capability



ELECTRICAL & ENVIRONMENTAL SPECIFICATIONS

Frequency:	1100-1700 MHz
Output Power:	150W min.
Nominal Gain:	53dB
Gain Flatness:	± 2 dB
Input VSWR:	2:1 max.
Enable Speed:	5 μs max.
Load VSWR for Survival:	∞:1 for 1 min.
DC Supply Voltage:	28V
DC Current:	13.5 A Avg
Operating Case Temp.:	-40 °C to 85 °C
Storage Temperature:	-40 °C to 85 °C
Shock:	MIL-STD-810F/G
Vibration:	MIL-STD-810F/G

INTERFACES

RF Input:	SMA Female
RF Output:	N Female
9-PIN DSUB:	1) GND 2) GND 3) 28 V 4) Enable 5) Reverse Power 6) GND 7) 28 V 8) 28 V 9) Forward Power

MECHANICAL SPECIFICATIONS

Size (mm) :	153 × 103.4 × 22.5
(inch) :	6 × 4.07 × 0.88
Weight :	610 gr.
Plating :	Yellow Chromate

